SPECIFICATION

General Description

The EM39LV800 is an 8M bits Flash memory organized as 512K x 16 bits. The EM39LV800 uses 2.7-3.6V power supply for Program and Erase. Featuring high performance Flash memory technology, the EM39LV800 provides a typical Word-Program time of 14 µsec and a typical Sector/Block-Erase time of 18 ms. The device uses Toggle Bit or Data# Polling to detect the completion of the Program or Erase operation. To protect against inadvertent write, the device has on-chip hardware and software data protection schemes. The device offers typical 100,000 cycles endurance and a greater than 10 years data retention. The EM39LV800 conforms with the JEDEC standard pin outs for x16 memories. The EM39LV800 is offered in package types of 48-ball FBGA, 48-pin TSOP, and known good dice (KGD). For KGD, please contact ELAN Microelectronics or its representatives for detailed information (see Appendix at the bottom of this specification for Ordering Information).

The EM39LV800 devices are developed for applications that require memories with convenient and economical updating of program, data or configuration, e.g., DVD player, DVD R/W, WLAN, Router, Set-Top Box, etc.

Features

- **Single Power Supply**
  Full voltage range from 2.7 to 3.6 volts for both read and write operations
- **Sector-Erase Capability**
  Uniform 2Kword sectors
- **Block-Erase Capability**
  Uniform 32Kword blocks
- **Read Access Time**
  Access time: 55, 70 and 90 ns
- **Power Consumption**
  Active current: 20 mA (Typical)
  Standby current: 2 µA (Typical)
- **Erase/Program Features**
  Sector-Erase Time: 18 ms (Typical)
  Block-Erase Time: 18 ms (Typical)
  Chip-Erase Time: 45 ms (Typical)
  Word-Program Time: 14µs (Typical)
  Chip Rewrite Time: 8 seconds (Typical)
- **Automatic Write Timing**
  Internal V_{PP} Generation
- **End-of-Program or End-of-Erase Detection**
  Data# Polling
  Toggle Bit
- **CMOS I/O Compatibility**
- **JEDEC Standard**
  Pin-out and software command sets compatible with single-power supply Flash memory
- **High Reliability**
  Endurance cycles: 100K (Typical)
  Data retention: 10 years
- **Package Option**
  48-pin TSOP
  48-pin FBGA

Functional Block Diagram

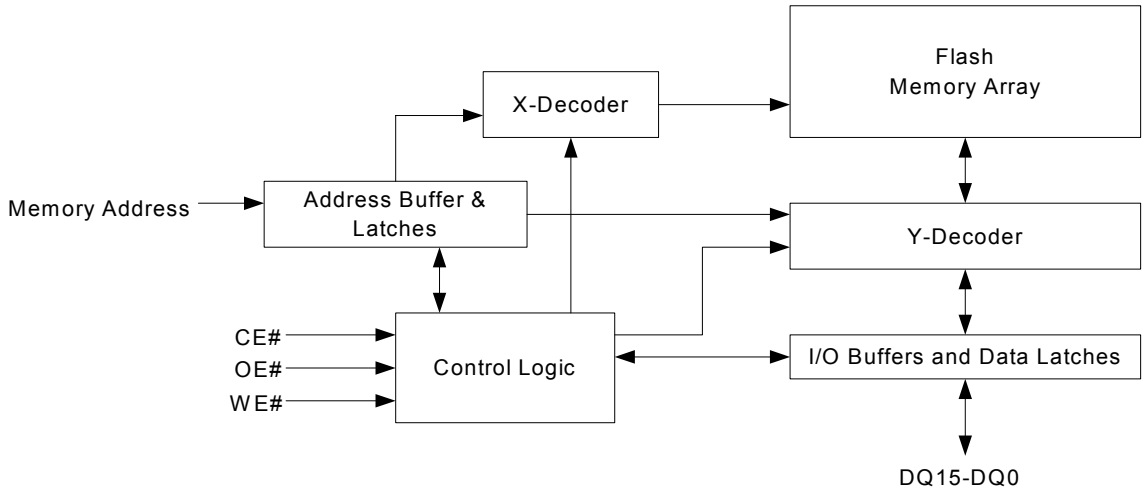


Figure 0a: *Functional Block Diagram*

Pin Assignments

TSOP

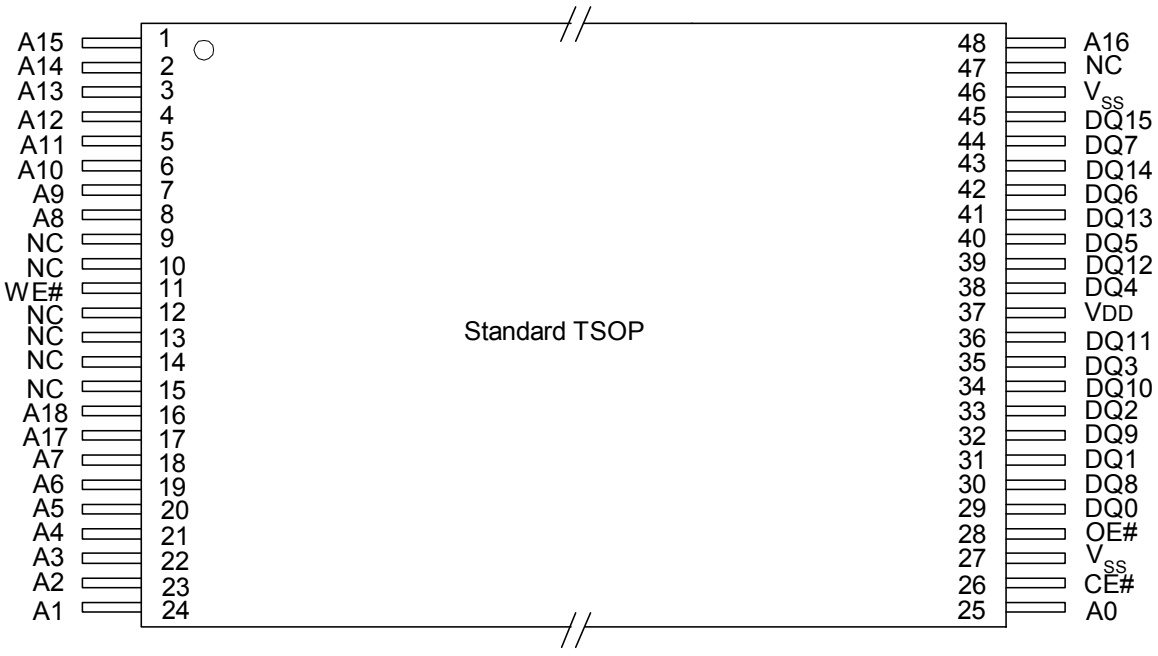


Figure 0b: *TSOP Pin Assignments*

FBGA

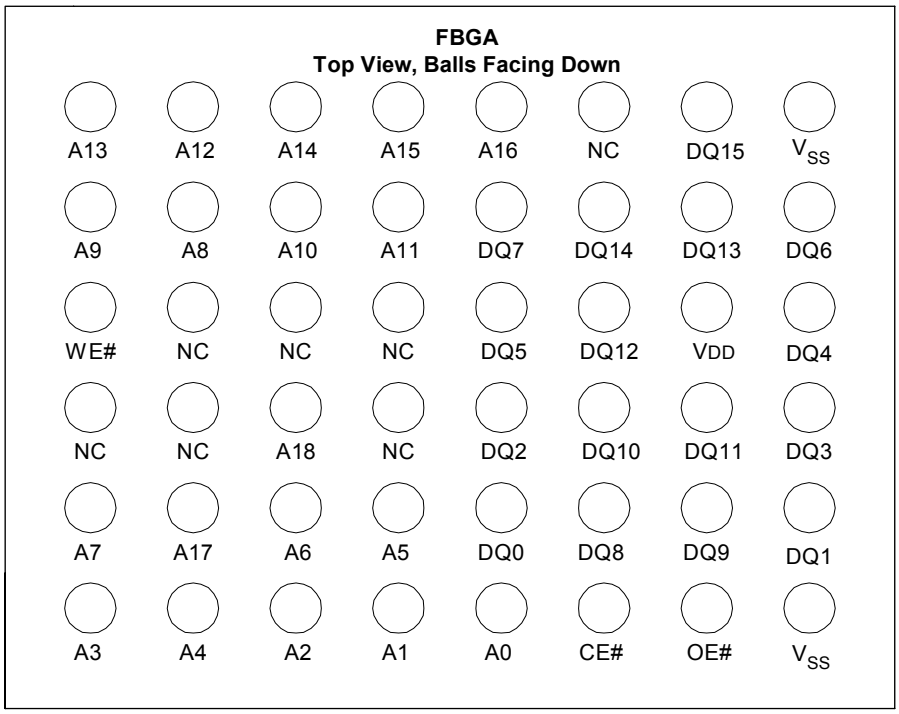


Figure 0c: *FBGA Pin Assignments*

Pin Description

Pin Name	Function
A0–A18	19 addresses
DQ15–DQ0	Data inputs/outputs
CE#	Chip enable
OE#	Output enable
WE#	Write enable
V_{DD}	2.7 ~ 3.6 volt single power supply
V_{SS}	Device ground
NC	Pin not connected internally

Table 1: *Pin Description*

Device Operation

The EM39LV800 uses Commands to initiate the memory operation functions. The Commands are written to the device by asserting WE# Low while keeping CE# Low. The address bus is latched on the falling edge of WE# or CE#, whichever occurs last. The data bus is latched on the rising edge of WE# or CE#, whichever occurs first.

Read

The Read operation of the EM39LV800 is controlled by CE# and OE#. Both have to be Low for the system to obtain data from the outputs. CE# is used for device selection. When CE# is high, the chip is deselected and only standby power is consumed. OE# is the output control and is used to gate data from the output pins. The data bus is in high impedance state when either CE# or OE# is high. Refer to the Read Cycle Timing Diagram in Figure 1 for further details.

Word Program

The EM39LV800 is programmed on a word-by-word basis. Before programming, the sector where the word is located must be erased completely. The Program operation is accomplished in three steps**:**

- The first step is a three-byte load sequence for Software Data Protection.
- The second step is to load word address and word data. During the Word Program operation, the addresses are latched on the falling edge of either CE# or WE#, whichever occurs last; and the data is latched on the rising edge of either CE# or WE#, whichever occurs first.
- The third step is the internal Program operation which is initiated after the rising edge of the fourth WE# or CE#, whichever occurs first. The Program operation, once initiated, will be completed within 20 µs. See Figures 2 and 3 for WE# and CE# controlled Program operation timing diagrams respectively and Figure 15 for flowchart.

During the Program operation, the only valid reads are Data# Polling and Toggle Bit. During the internal Program operation, the host is free to perform additional tasks. Any command issued during the internal Program operation is ignored.

EM39LV800 Device Operation

Operation	CE#	OE#	WE#	DQ	Address
Read	V_{IL}	V_{IL}	V_{IH}	D_{OUT}	A_{IN}
Program	V_{IL}	V_{IH}	V_{IL}	D_{IN}	A_{IN}
Erase	V_{IL}	V_{IH}	V_{IL}	X*	Sector or Block address, XXH for Chip-Erase
Standby	V_{IH}	X	X	High Z	X
Write Inhibit	X	V_{IL}	X	High Z/D_{OUT}	X
Write Inhibit	X	X	V_{IH}	High Z/D_{OUT}	X
Software Mode	V_{IL}	V_{IL}	V_{IH}		See Table 3
Product Identification					

** X can be V_{IL} or V_{IH}, but no other value.*

Table 2: *EM39LV800 Device Operation*

Write Command/Command Sequence

The EM39LV800 provides two software methods to detect the completion of a Program or Erase cycle in order to optimize the system write cycle time. The software detection includes two status bits**:** Data# Polling (DQ7) and Toggle Bit (DQ6). The End-of-Write detection mode is enabled after the rising edge of WE#, which initiates the internal Program or Erase operation. The actual completion of the write operation is asynchronous with the system; therefore, either a Data# Polling or Toggle Bit read may be simultaneous with the completion of the write cycle. If this occurs, the system may possibly get an erroneous result, i.e., valid data may appear to conflict with either DQ7 or DQ6. In order to prevent such spurious rejection, when an erroneous result occurs, the software routine should include an additional two times loop to read the accessed location. If both reads are valid, then the device has completed the write cycle, otherwise the rejection is valid.

Chip Erase

The EM39LV800 provides Chip-Erase feature, which allows the entire memory array to be erased to logic “1” state. The Chip-Erase operation is initiated by executing a six-byte command sequence with Chip-Erase command (10H) at address 5555H in the last byte sequence. The Erase operation begins with the rising edge of the sixth WE# or CE#, whichever occurs first. During the Erase operation, the only valid reads are Toggle Bit and Data# Polling. See Table 3 for the command sequence, Figure 6 for timing diagram, and Figure 17 for the flowchart. Any commands issued during the Chip-Erase operation are ignored.

Sector/Block Erase

The EM39LV800 offers both Sector-Erase and Block-Erase modes. The Sector- (or Block-) Erase operation allows the system to erase the device on a sector-by-sector (or block-by-block) basis. The sector architecture is based on uniform sector size of 2 KWord. The Block architecture is based on uniform block size of 32 KWord. The Sector-Erase operation is initiated by executing a six-byte command sequence with Sector-Erase command (30H) and sector address (SA) in the last bus cycle. The Block-Erase operation is initiated by executing a six-byte command sequence with Block-Erase command (50H) and block address (BA) in the last bus cycle. The sector or block address is latched on the falling edge of the sixth WE# pulse, while the command (30H or 50H) is latched on the rising edge of the sixth WE# pulse. The internal Erase operation begins after the sixth WE# pulse. The End-of-Erase operation can be determined by using either Data# Polling or Toggle Bit method. See Figures 7 and 8 for timing waveforms. Any commands issued during the Sector or Block Erase operation are ignored.

Data# Polling (DQ7)

When the EM39LV800 is in the internal Program operation, any attempt to read DQ7 will produce the complement of the true data. Once the Program operation is completed, DQ7 will produce the true data. Note that even though DQ7 may have valid data immediately following the completion of an internal Program operation, the remaining data outputs may still be invalid (valid data on the entire data bus will appear in subsequent successive Read cycles after an interval of 1 μs). During internal Erase operation, any attempt to read DQ7 will produce a '0'. Once the internal Erase operation is completed, DQ7 will produce a '1'. The Data# Polling is valid after the rising edge of fourth WE# (or CE#) pulse for Program operation. For Sector-Erase, Block-Erase, or Chip-Erase, the Data# Polling is valid after the rising edge of sixth WE# (or CE#) pulse. See Figure 4 for Data# Polling timing diagram and Figure 14 for a flowchart.

Toggle Bit (DQ6)

During the internal Program or Erase operation, any consecutive attempts to read DQ6 will produce alternating 1s and 0s, i.e., toggling between 1 and 0. When the internal Program or Erase operation is completed, the DQ6 bit will stop toggling. The device is then ready for the next operation. The Toggle Bit is valid after the rising edge of fourth WE# (or CE#) pulse for Program operation. For Sector-Erase, Block-Erase or Chip-Erase, the Toggle Bit is valid after the rising edge of sixth WE# (or CE#) pulse. See Figure 5 for Toggle Bit timing diagram and Figure 14 for a flowchart.

Data Protection

The EM39LV800 provides both hardware and software features to protect the data from inadvertent write.

Hardware Data Protection

Noise/Glitch Protection: A WE# or CE# pulse of less than 5 ns will not initiate a write cycle.

V_{DD} Power Up/Down Detection: The Write operation is inhibited when V_{DD} is less than 1.5V.

Write Inhibit Mode: Forcing OE# Low, CE# High, or WE# High will inhibit the Write operation. This prevents inadvertent write during power-up or power-down.

Software Data Protection (SDP)

The EM39LV800 provides the JEDEC approved Software Data Protection (SDP) scheme for Program and Erase operations. Any Program operation requires the inclusion of the three-byte sequence. The three-byte load sequence is used to initiate the Program operation, providing optimal protection from inadvertent Write operations, especially during the system power-up or power-down transition. Any Erase operation requires the inclusion of six-byte sequence. See Table 3 for the specific software command codes. During SDP command sequence, invalid commands will abort the device to Read mode within T_{RC}. The contents of DQ15-DQ8 can be V_{IL} or V_{IH}, but no other value, during any SDP command sequence.

Common Flash Memory Interface (CFI)

The EM39LV800 contains the CFI information to describe the characteristics of the device. In order to enter the CFI Query mode, the system must write three-byte sequence, same as Software ID Entry command, with 98H (CFI Query command) to address 5555H in the last byte sequence. Once the device enters the CFI Query mode, the system can read CFI data at the addresses given in Tables 4 through 6. The system must write the CFI Exit command to return to Read mode from the CFI Query mode.

Software Command Sequence

Command Sequence	1st Bus Write Cycle		2nd Bus Write Cycle		3rd Bus Write Cycle		4th Bus Write Cycle		5th Bus Write Cycle		6th Bus Write Cycle	
	Addr[1]	Data[2]	Addr[1]	Data[2]	Addr[1]	Data[2]	Addr[1]	Data[2]	Addr[1]	Data[2]	Addr[1]	Data[2]
Word Program	5555H	AAH	2AAAH	55H	5555H	A0H	WA[3]	Data				
Sector Erase	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	SA_X[4]	30H
Block Erase	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	BA_X[4]	50H
Chip Erase	5555H	AAH	2AAAH	55H	5555H	80H	5555H	AAH	2AAAH	55H	5555H	10H
Software ID Entry[5,6]	5555H	AAH	2AAAH	55H	5555H	90H						
Manufacture ID	5555H	AAH	2AAAH	55H	5555H	90H	0000H	0007F				
Manufacture ID	5555H	AAH	2AAAH	55H	5555H	90H	0003H	0007F				
Manufacture ID	5555H	AAH	2AAAH	55H	5555H	90H	0040H	0001F				
Device ID	5555H	AAH	2AAAH	55H	5555H	90H	0001H	0020H				
CFI Query Entry[5]	5555H	AAH	2AAAH	55H	5555H	98H						
Software ID Exit[7]/CFI Exit	XXH	F0H										
Software ID Exit[7]/CFI Exit	5555H	AAH	2AAAH	55H	5555H	F0H						

Notes:

1. *Address format A14-A0 (Hex), Addresses A18-A15 can be V_{IL} or V_{IH}, but no other value, for the Command sequence.*
2. *DQ15-DQ8 can be V_{IL} or V_{IH}, but no other value, for the Command sequence.*
3. *WA = Program word address.*
4. *SA_X for Sector-Erase; uses A18-A11 address lines.*
   BA_X for Block-Erase; uses A18-A15 address lines.
5. *The device does not remain in Software Product ID mode if powered down.*
6. *Both Software ID Exit operations are equivalent.*
7. *Refer to Figure 9 for more information.*

Table 3: *Software Command Sequence*

CFI Query Identification String*

Address	Data	Data
10H 11H 12H	0051H 0052H 0059H	Query Unique ASCII string “QRY”
13H 14H	0001H 0007H	Primary OEM command set
15H 16H	0000H 0000H	Address for Primary Extend Table
17H 18H	0000H 0000H	Alternate OEM command set (00H=none exists)
19H 1AH	0000H 0000H	Address for Alternate OEM extended Table (00H=none exists)

***** *Refer to CFI publication 100 for more details.*

Table 4: *CFI Query Identification String1*

System Interface

Address	Data	Data
1BH	0027H	V_{DD} Min (Program/Erase) DQ7-DQ4: Volts, DQ3-DQ0: 100 millivolts
1CH	0036H	V_{DD} Max (Program/Erase) DQ7-DQ4: Volts, DQ3-DQ0: 100 millivolts
1DH	0000H	V_{PP} min (00H=no V_{PP} pin)
1EH	0000H	V_{PP} max (00H=no V_{PP} pin)
1FH	0004H	Typical time out for Word-Program 2^N μs (2^4=16μs)
20H	0000H	Typical time out for min size buffer program 2^N μs (00H=not supported)
21H	0004H	Typical time out for individual Sector/Block-Erase 2^N ms (2^4=16ms)
22H	0006H	Typical time out for Chip-Erase 2^N ms (2^6=64ms)
23H	0001H	Maximum time out for Word-Program 2^N times typical (2^1x2^4=32μs)
24H	0000H	Maximum time out for buffer Program 2^N times typical
25H	0001H	Maximum time out for individual Sector/Block-Erase 2^N times typical (2^1x2^4=32ms)
26H	0001H	Maximum time out for Chip-Erase 2^N times typical (2^1x2^6=128ms)

Table 5: *System Interface*

Device Geometry Information

Address	Data	Data
27H	0014H	Device size=2^N Byte (14H=20; 2^{20}=1MByte)
28H 29H	0001H 0000H	Flash Device Interface description; 0001H=x16-only asynchronous interface
2AH 2BH	0000H 0000H	Maximum number of byte in multi-byte write=2^N (00H=not supported)
2CH	0002H	Number of Erase Sector/Block sizes supported by device
2DH 2EH 2FH 30H	00FFH 0000H 0010H 0000H	Sector Information (y+1=Number of sectors; z x 256B=sector size) y=255+1=256 sectors (00FFH=255) z=16 x 256 Bytes=4Kbyte/sector (0010H=16)
31H 32H 33H 34H	000FH 0000H 0000H 0001H	Block Information (y+1=Number of blocks; z x 256B=block size) y=15+1=16 blocks (000FH=15) z=256 x 256 Bytes=64 Kbyte/block (0100H=256)

Table 6: *Device Geometry Information*

Absolute Maximum Ratings

NOTE

Applied conditions greater than those listed under these ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this specification, are not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.

Temperature Under Bias ..... –55°C to 125°C

Storage Temperature ..... –65°C to 150°C

D.C. Voltage on Any Pin to Ground Potential ..... –0.5 V to V_{DD}+0.5V

Transient Voltage (<20ns) on Any Pin to Ground Potential ..... –2.0V to V_{DD} +2.0V

Voltage on A9 Pin to Ground Potential ..... –0.5 V to 13.2V

Package Power Dissipation Capability (Ta=25°C)..... 1.0W

Surface Mount Lead Soldering Temperature (3 Seconds)..... 240°C

Output Short Circuit Current * 50mA

* *Output shorted for no more than one second. No more than one output shorted at a time.*

Operating Range

Model Name	Ambient Temperature	V_{DD}
EM39LV800	0°C to +70°C	2.7~3.6V

Table 7: *Operating Range*

AC Conditions of Test

Input Rise/Fall Time 5ns

Output Load ..... CL=30pF for 55Rns

Output Load ..... CL=100pF for 70ns/90ns

See Figures 14 and 15

DC CHARACTERISTICS (CMOS Compatible)

Parameter	Description	Test Conditions	Min	Max	Unit
I_{DD}	Power Supply Current	Address Input =V_{IL}/V_{IH}, at f=1/T_{RC} Min, $V_{DD}=V_{DD}$ Max			
	Read	CE#=OE#=V_{IL}, WE#=V_{IH}, all I/Os open		30	mA
	Program and Erase	CE#=WE#=V_{IL}, OE#=V_{IH},		30	mA
I_{SB}	Standby V_{DD} Current	CE#=V_{IHC}, $V_{DD}=V_{DD}$ Max		20	µA
I_{LI}	Input Leakage Current	V_{IN}=GND to V_{DD}, $V_{DD}=V_{DD}$ Max		1	µA
I_{LO}	Output Leakage Current	V_{OUT}=GND to V_{DD}, $V_{DD}=V_{DD}$ Max		10	µA
V_{IL}	Input Low Voltage	$V_{DD}=V_{DD}$ Min		0.8	V
V_{IH}	Input High Voltage	$V_{DD}=V_{DD}$ Max	0.7 V_{DD}		V
V_{IHC}	Input High Voltage (CMOS)	$V_{DD}=V_{DD}$ Max	V_{DD}-0.3		V
V_{OL}	Output Low Voltage	I_{OL}=100µA, $V_{DD}=V_{DD}$ Min		0.2	V
V_{OH}	Output High Voltage	I_{OH}=-100µA, $V_{DD}=V_{DD}$ Min	V_{DD}-0.2		V

Table 8: *DC Characteristics (Cmos Compatible)*

Recommended System Power-up Timing

Parameter	Description	Min	Unit
$T_{PU-READ}$*	Power-up to Read Operation	100	µs
$T_{PU-WRITE}$*	Power-up to Program/Erase Operation	100	µs

***** *This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.*

Table 9: *Recommended System Power-up Timing*

Capacitance (Ta=25°C, f=1Mhz, other pins open)

Parameter	Description	Test Conditons	Max
$C_{I/O}$*	I/O Pin Capacitance	$V_{I/O}$=0V	12pF
C_{IN}*	Input Capacitance	V_{IN}=0V	6pF

* *This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.*

Table 10: *Capacitance (Ta=25°C, f=1Mhz, Other Pins Open)*

Reliability Characteristics

Symbol	Parameter	Min Specification	Unit	Test Method
N_{END}*	Endurance	10,000	Cycles	JEDEC Standard A117
T_{DR}*	Data Retention	10	Years	JEDEC Standard A103
I_{LTH}*	Latch Up	100+I_{DD}	mA	JEDEC Standard 78

* *This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.*

Table 11: *Reliability Characteristics*

AC Characteristics

Read Cycle Timing Parameters

Symbol	Parameter	55REC		70REC		90REC		Unit
		Min	Max	Min	Max	Min	Max	
T_{RC}	Read Cycle Time	55		70		90		ns
T_{CE}	Chip Enable Access Time		55		70		90	ns
T_{AA}	Address Access Time		55		70		90	ns
T_{OE}	Output Enable Access Time		30		35		45	ns
T_{CLZ}*	CE# Low to Active Output	0		0		0		ns
T_{OLZ}*	OE# Low to Active Output	0		0		0		ns
T_{CHZ}*	CE# High to High-Z Output		15		20		30	ns
T_{OHZ}*	OE# High to High-Z Output		15		20		30	ns
T_{OH}*	Output Hold from Address Change	0		0		0		ns

* *This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.*

Table 12a: *Read Cycle Timing Parameters*

Symbol	Parameter	55EC		70EC		90EC		Unit
		Min	Max	Min	Max	Min	Max	
T_{RC}	Read Cycle Time	55		70		90		ns
T_{CE}	Chip Enable Access Time		55		70		90	ns
T_{AA}	Address Access Time		55		70		90	ns
T_{OE}	Output Enable Access Time		30		35		45	ns
T_{CLZ}*	CE# Low to Active Output	0		0		0		ns
T_{OLZ}*	OE# Low to Active Output	0		0		0		ns
T_{CHZ}*	CE# High to High-Z Output		15		20		30	ns
T_{OHZ}*	OE# High to High-Z Output		15		20		30	ns
T_{OH}*	Output Hold from Address Change	0		0		0		ns

* *This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.*

Table 12b: *Read Cycle Timing Parameters*

Program/Erase Cycle Timing Parameter

Symbol	Parameter	Min	Max	Unit
T_{BP}	Word-Program Time		20	μs
T_{AS}	Address Setup Time	0		ns
T_{AH}	Address Hold Time	30		ns
T_{CS}	WE# and CE# Setup Time	0		ns
T_{CH}	WE# and CE# Hold Time	0		ns
T_{OES}	OE# High Setup Time	0		ns
T_{OEH}	OE# High Hold Time	10		ns
T_{CP}	CE# Pulse Width	45		ns
T_{WP}	WE# Pulse Width	45		ns
T_{WPH}*	WE# Pulse Width High	30		ns
T_{CPH}*	CE# Pulse Width High	30		ns
T_{DS}	Data Setup Time	45		ns
T_{DH}*	Data Hold Time	0		ns
T_{IDA}*	Software ID Access and Exit Time		150	ns
T_{SE}	Sector Erase		30	ms
T_{BE}	Block Erase		30	ms
T_{SCE}	Chip Erase		60	ms

* *This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.*

Table 13: *Program/Erase Cycle Timing Parameter*

Timing Diagrams

Read Cycle Timing Diagram

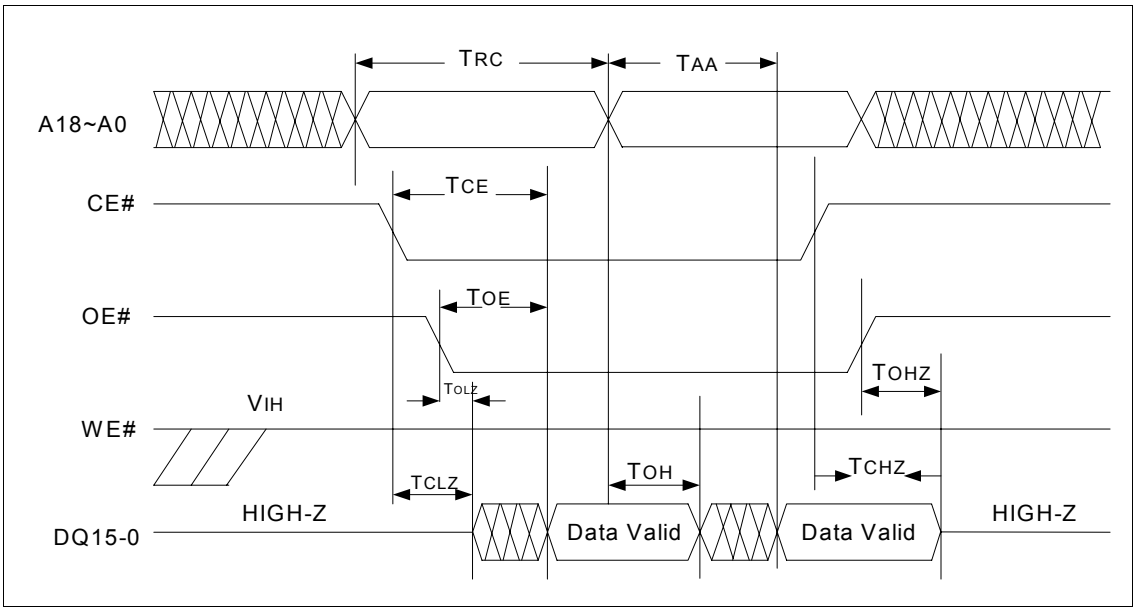


Figure 1: *Read Cycle Timing Diagram*

WE# Controlled Program Cycle Timing Diagram

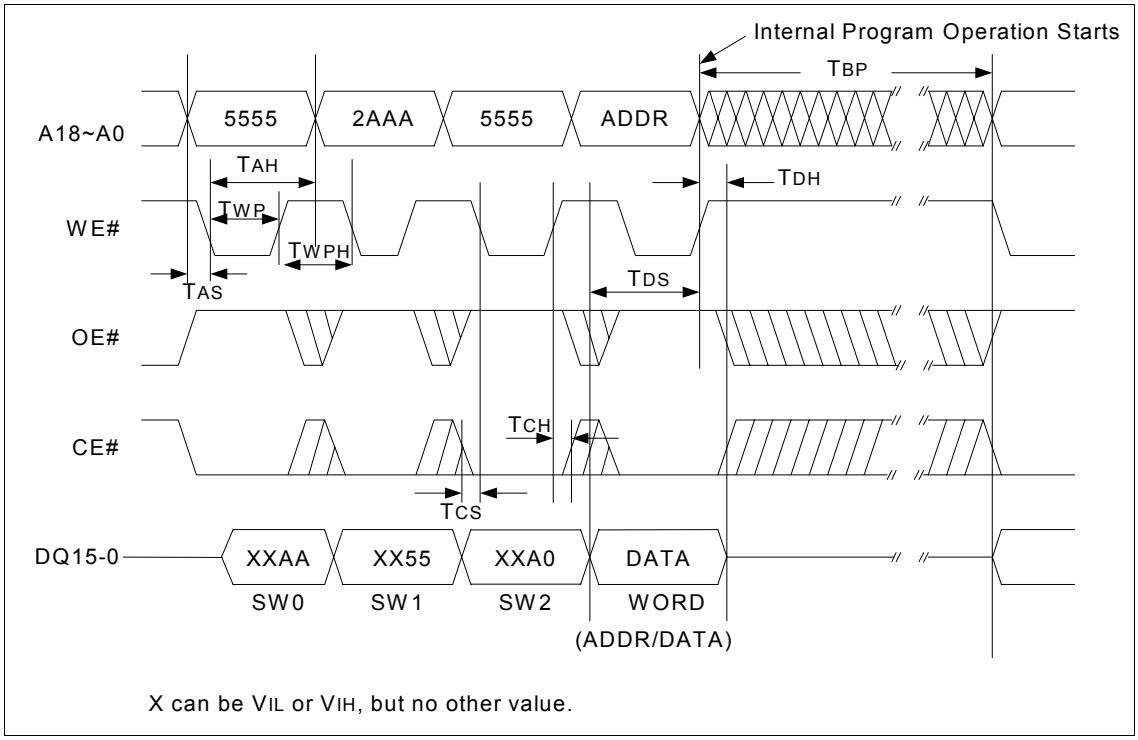


Figure 2: *WE# Controlled Program Cycle Timing Diagram*

CE# Controlled Program Cycle Timing Diagram

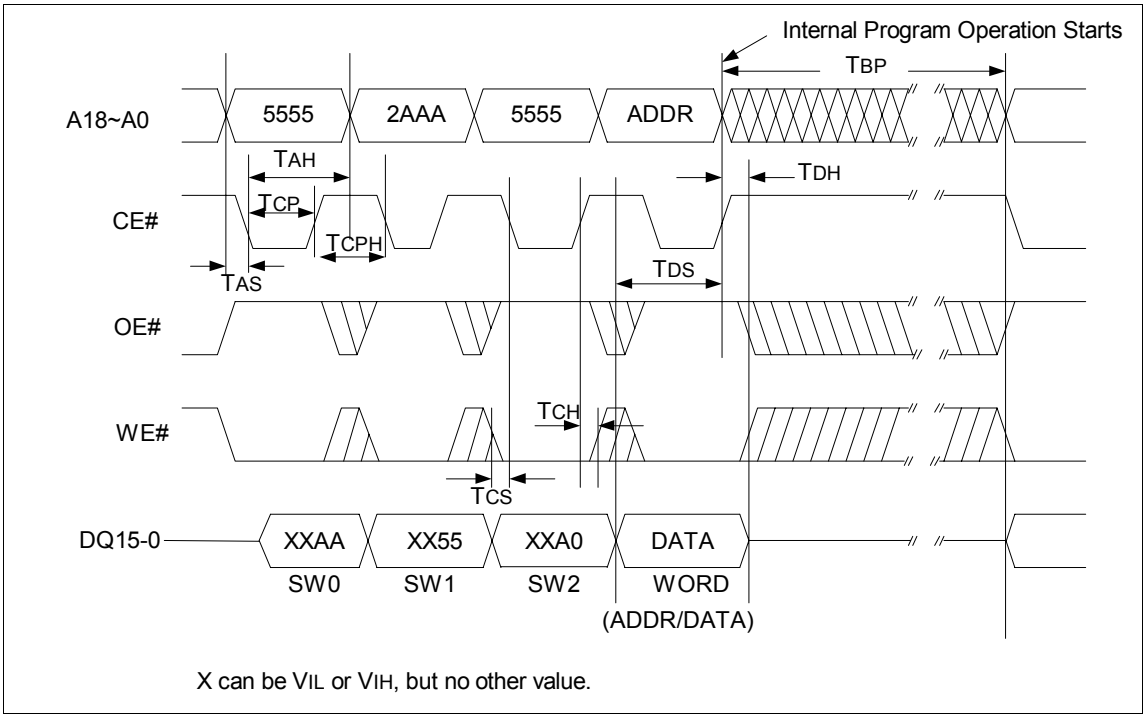


Figure 3: *CE# Controlled Program Cycle Timing Diagram*

Data# Polling Timing Diagram

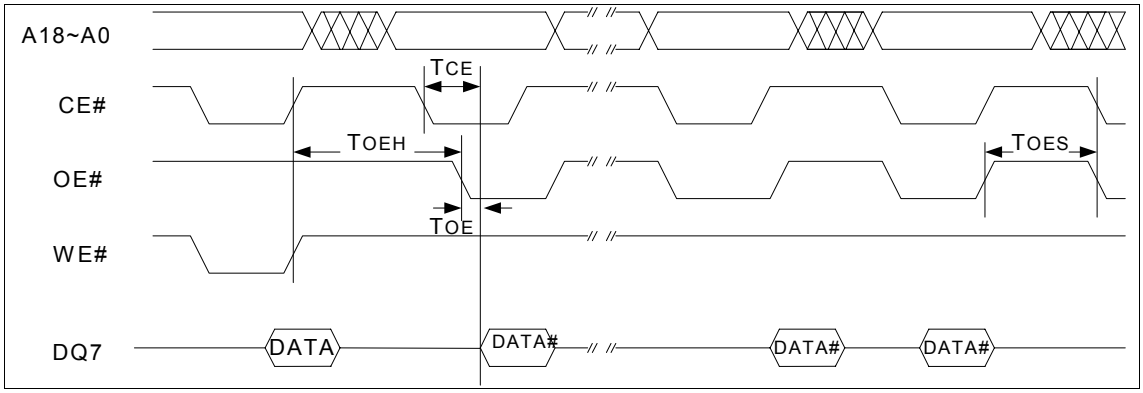


Figure 4: *Data# Polling Timing Diagram*

Toggle Bit Timing Diagram

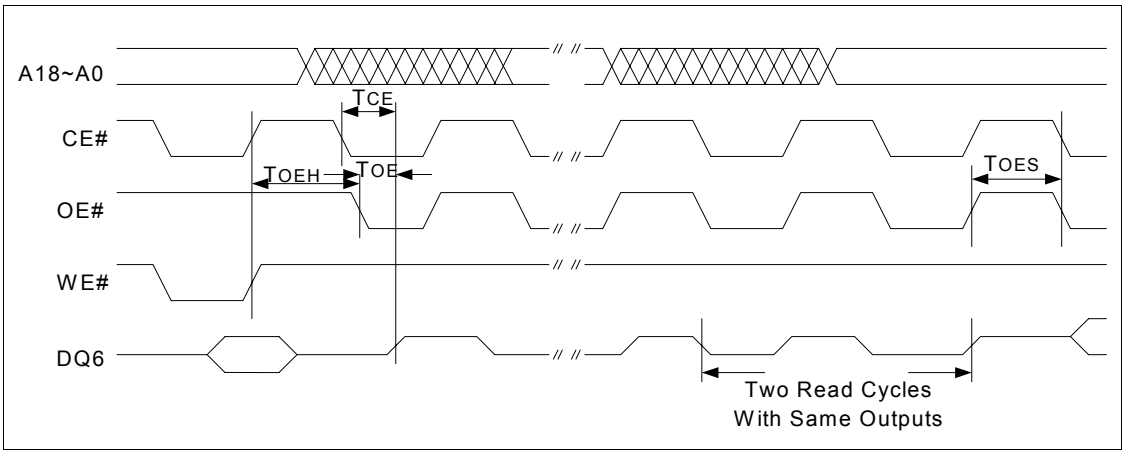
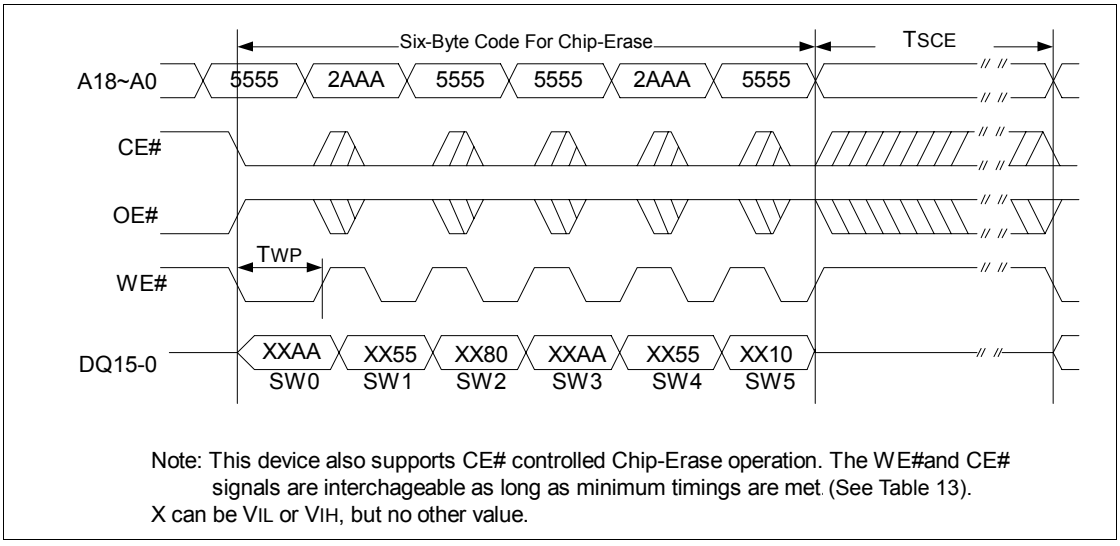


Figure 5: *Toggle Bit Timing Diagram*

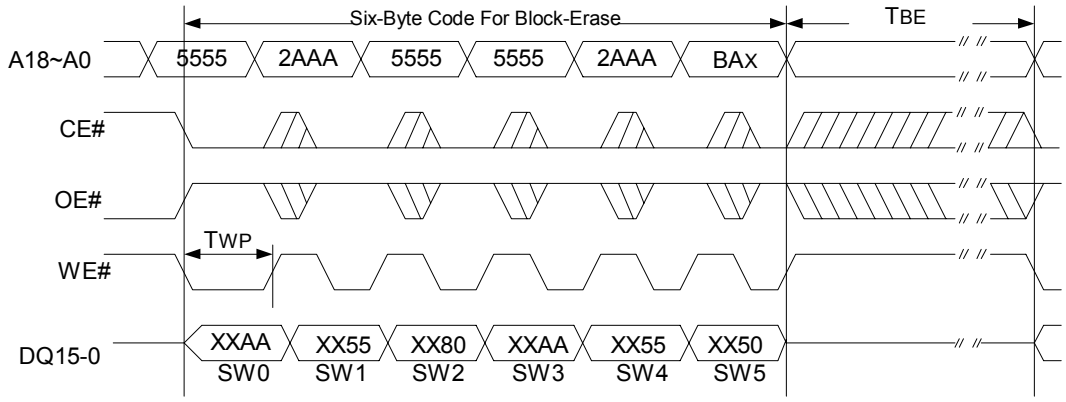
WE# Controlled Chip-Erase Timing Diagram



Note: This device also supports CE# controlled Chip-Erase operation. The WE#and CE# signals are interchageable as long as minimum timings are met. (See Table 13).
X can be VIL or VIH, but no other value.

Figure 6: *WE# Controlled Chip-Erase Timing Diagram*

WE# Controlled Block-Erase Timing Diagram



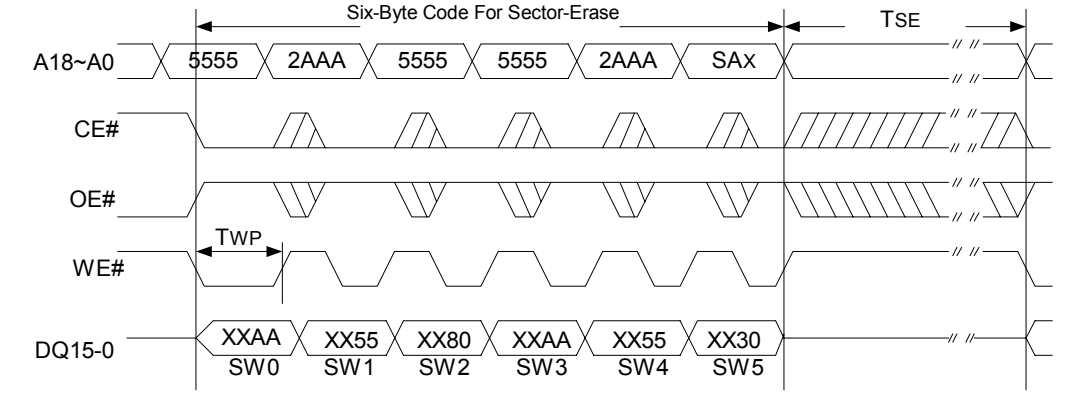
Note: This device also supports CE# controlled Block-Erase operation. The WE#and CE# signals are interchageable as long as minimum timings are met (See Table 13).

BAX=Block Address

X can be VIL or VIH, but no other value.

Figure 7: *WE# Controlled Block-Erase Timing Diagram*

WE# Controlled Sector-Erase Timing Diagram



Note: This device also supports CE# controlled Sector-Erase operation. The WE#and CE# signals are interchageable as long as minimum timings are met. (See Table 13).

SAX=Sector Address

X can be VIL or VIH, but no other value.

Figure 8: *WE# Controlled Sector-Erase Timing Diagram*

Software ID Entry and Read

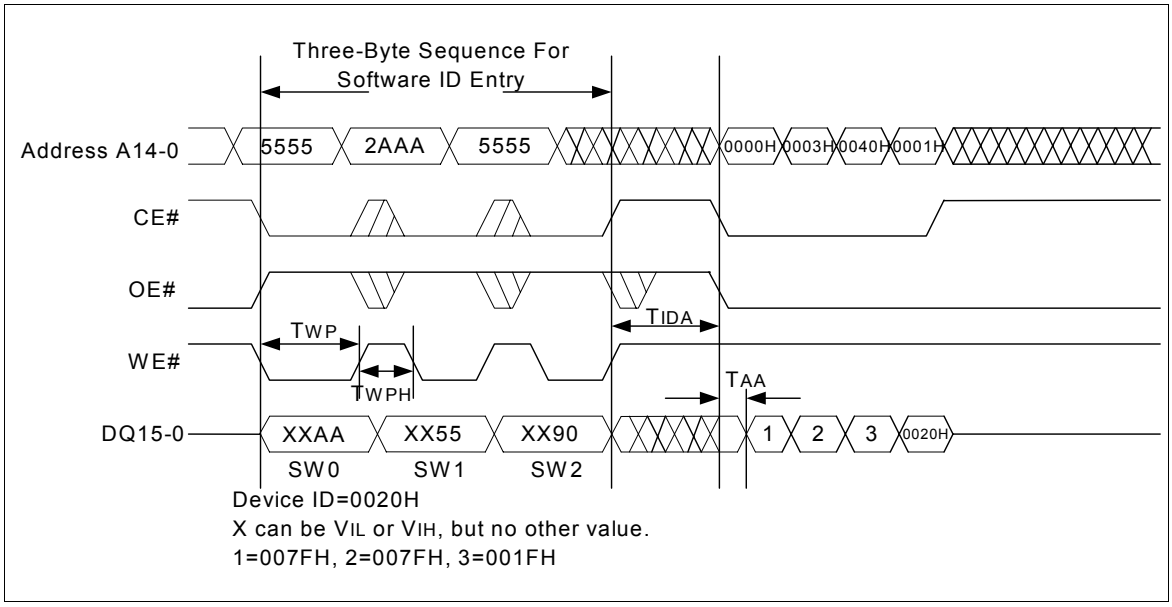


Figure 9: *Software ID Entry and Read*

CFI Query Entry and Read

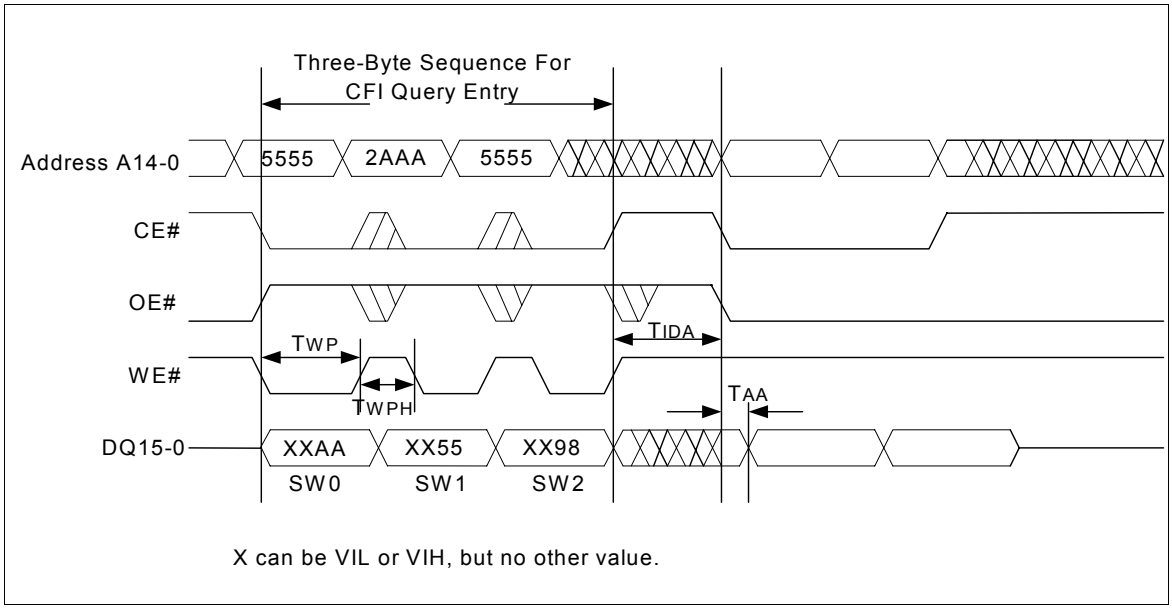


Figure 10: *CFI Query Entry and Read*

Software ID Exit/CFI Exit

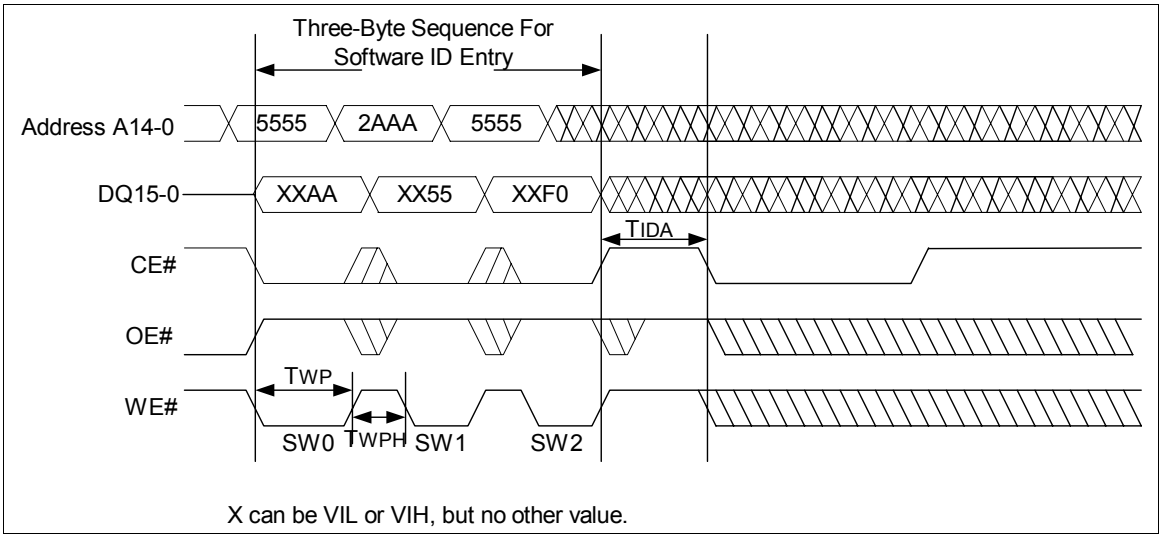
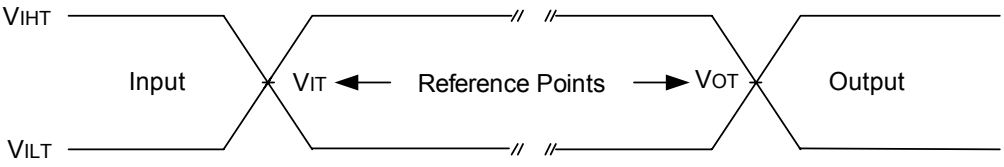


Figure 11: *Software ID Exit/CFI Exit*

AC Input/Output Reference Waveforms



AC test inputs are driven at V_{IHT} (0.9 V_{DD}) for a logic "1" and V_{ILT}(0.1 V_{DD}) for a logic "0". Measurement reference points for inputs and outpputs are V_{IT}(0.5 V_{DD}) and V_{OT}(0.5 V_{DD}). Input rise and fall times(10% - 90%) are <5ns

Note: V_{IT} = Vinput Test
V_{OT} = Voutput Test
V_{IHT} = Vinput HIGH Test
V_{ILT} = Vinput LOW Test

Figure 12: *AC Input/Output Reference Waveforms*

A Test Load Example

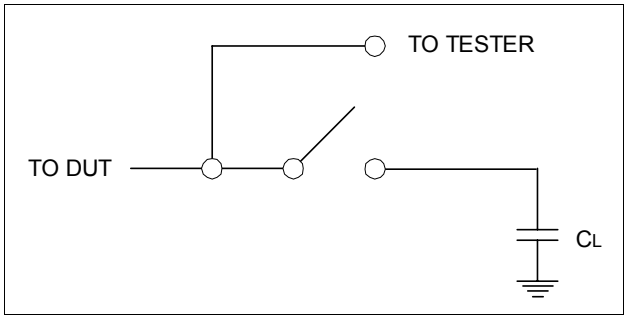


Figure 13: *A Test Load Example*

Flow Charts

Wait Options

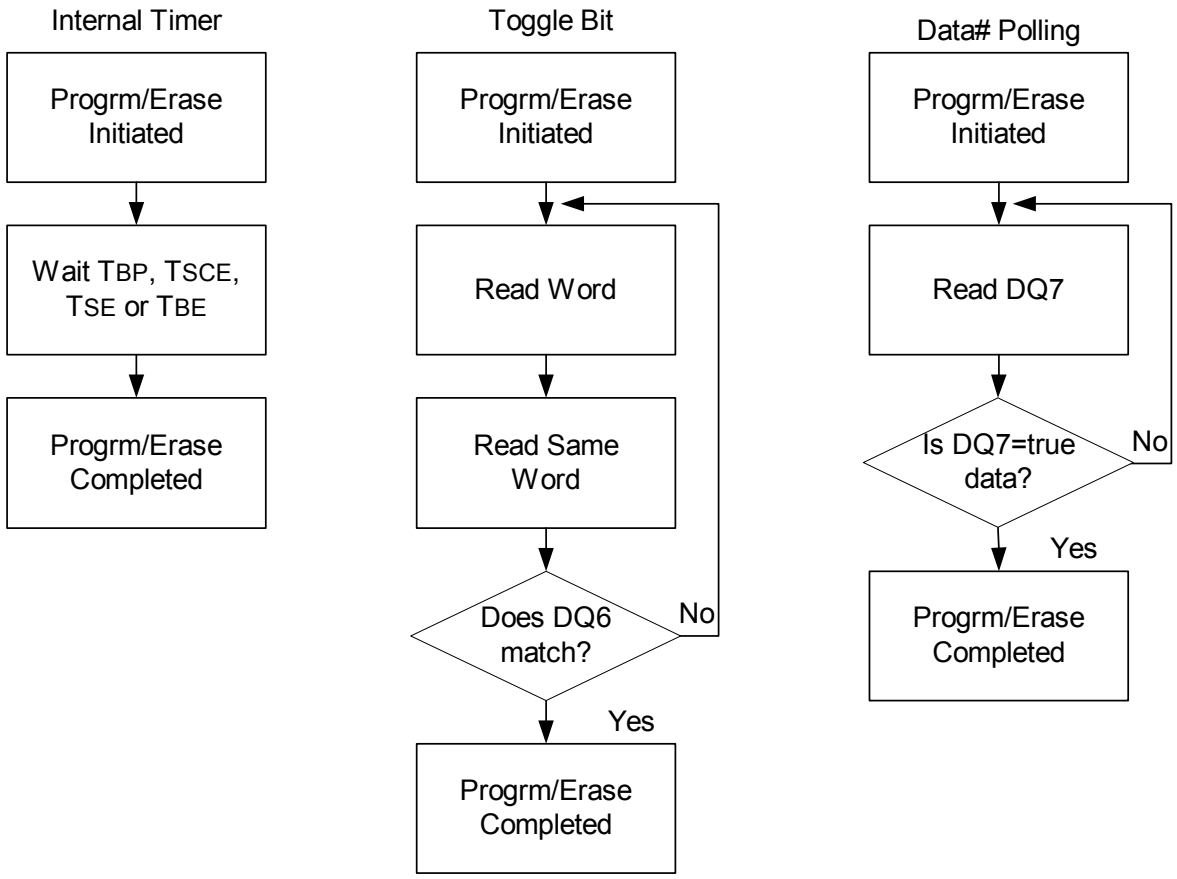
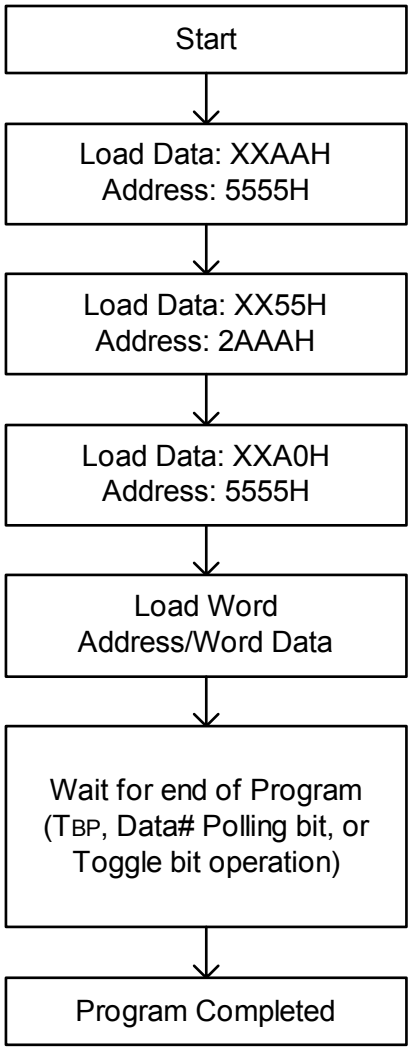


Figure 14: *Wait Options*

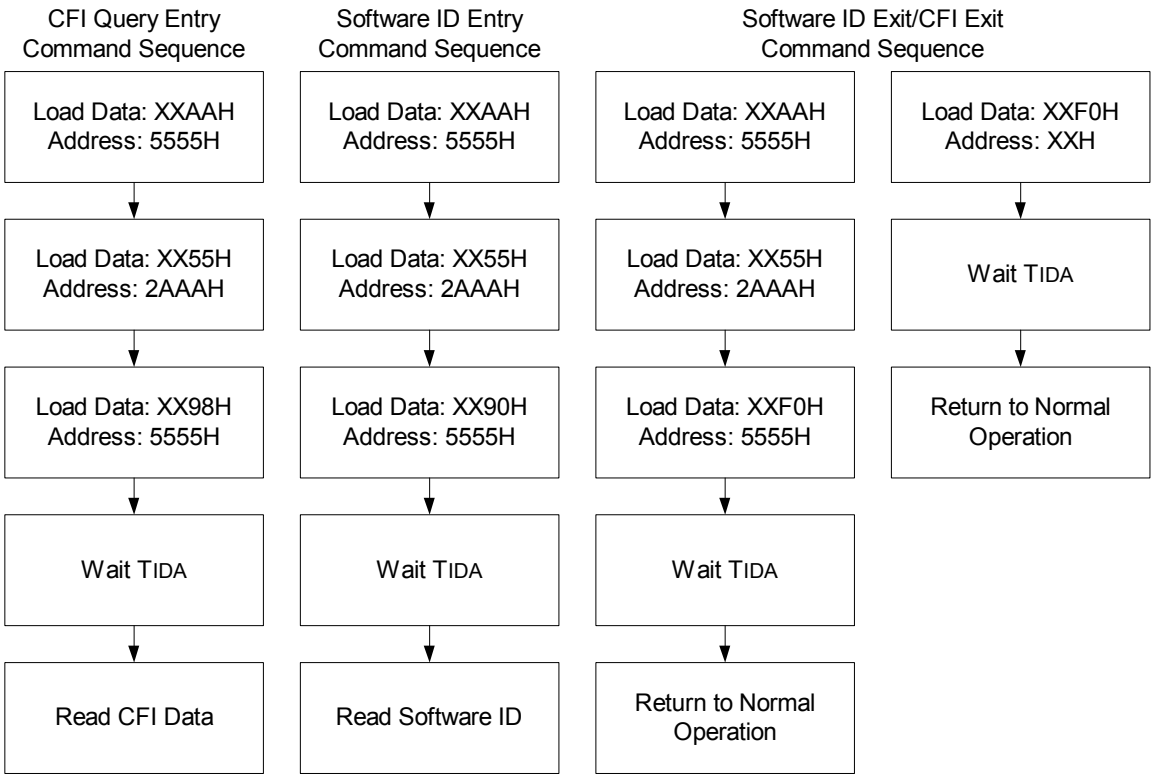
Word-Program Algorithm



X can be VIL or VIH, but no other value.

Figure 15: *Word-Program Algorithm*

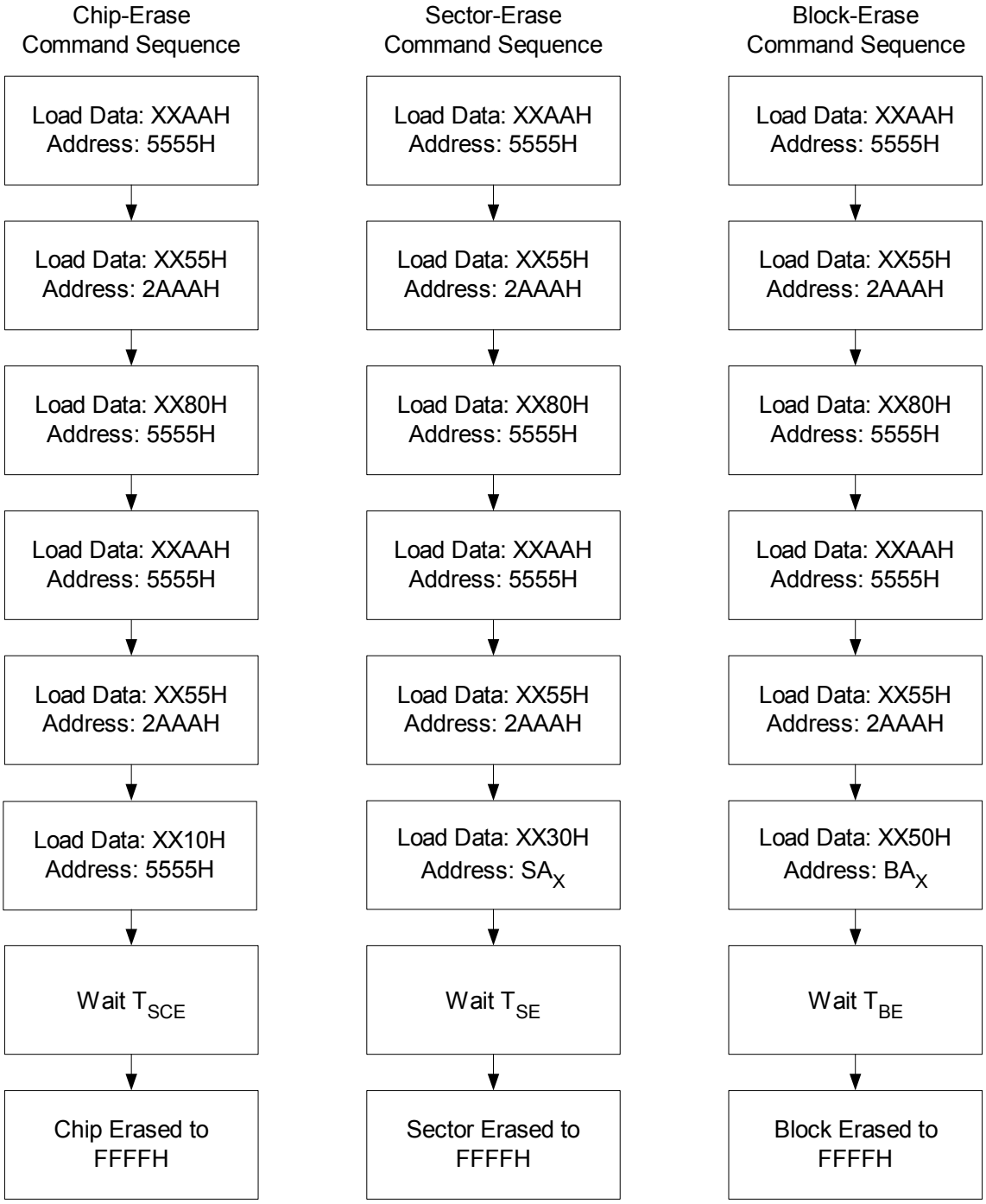
Software ID/CFI Command Flowcharts



X can be VIL or VIH, but no other value.

Figure 16: *Software ID/CFI Command Flowcharts*

Erase Command Sequence



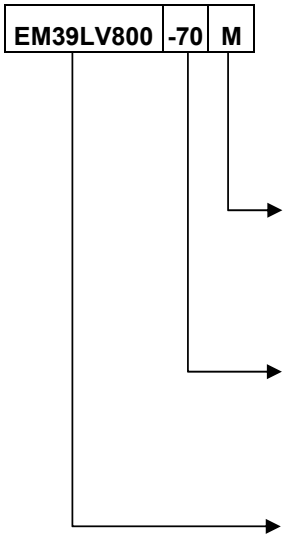
X can be VIL or VIH, but no other value.

Figure 17: *Erase Command Sequence*

Appendix

ORDERING INFORMATION (Standard Products)

The order number is defined by a combination of the following elements.



Description
Package Type (1 digit)
M = TSOP (Type 1, die up, 12mm x 20mm)
Y = FBGA (0.8mm pitch, 6mm x 8mm)
H = Chip Form
D = Known Good Dice (for wafer dice sell)
Speed Option (2-3 digits)
55R = 55ns
70 = 70ns
90 = 90ns
** = VDD = 2.7–3.6V
**R = VDD=3.0-3.6V
Device Number/Description
EM39LV800
8 Megabit (512K x 16-Bit) Flash Memory
2.7-3.6 Volt only Read, Program, and Erase

ORDERING INFORMATION (Non-Standard Products)

For Know Good Dice (KGD), please contact ELAN Microelectronics at the following contact information or its representatives.

ELAN MICROELECTRONICS CORPORATION

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Fax: +886 3 563-9966
http://www.emc.com.tw

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